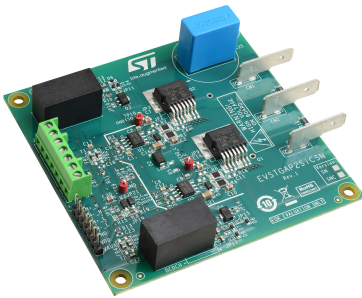


Demonstration board for STGAP2SICSNC isolated 4 A single gate driver



Features

- **Board**
 - Half bridge configuration, high voltage rail up to 520 V
 - SCT35N65: 650V, 55 mΩ SiC MOSFET
 - Negative gate driving
 - On board isolated DC-DC converters to supply high-side and low-side gate drivers, fed by VAUX = 5 V, with 5.2 kV maximum isolation
 - 3.3 V VDD logic supply generated onboard or 5 V (externally applied)
 - Easy jumper selection of driving voltage configuration: +17/0 V; +17/-3 V; +19/0 V; +19/-3 V
- **Device**
 - Driver current capability: 4 A source/sink @ 25 °C
 - 4 A Miller Clamp
 - Short propagation delay: 75 ns
 - UVLO function
 - Gate driving voltage up to 26 V
 - 3.3 V, 5 V TTL/CMOS inputs with hysteresis
 - Temperature shut down protection
 - Stand-by function

Description

The EVSTGAP2SICSNC is a half bridge evaluation board designed to evaluate the STGAP2SICSNC isolated single gate driver.

The gate driver is characterized by 4 A current capability and rail-to-rail outputs, making the device suitable also for high power inverter applications such as motor drivers in industrial applications equipped with SiC power switch.

The configuration featuring single output pin and Miller CLAMP function allow avoiding gate spikes during fast commutations in half-bridge topologies.

The device integrates protection functions: UVLO and thermal shut down are included to easily design high reliability systems. Dual input pins allow choosing the control signal polarity and implementing HW interlocking protection to avoid cross-conduction in case of controller's malfunction.

The device allows implementing negative gate driving, and the onboard isolated DC-DC converters allow working with optimized driving voltage for SiC.

The EVSTGAP2SICSNC board allows evaluating all the STGAP2SICSNC features while driving a half-bridge power stage with voltage rating up to 520 V. It is possible to increase bus voltage by replacing the power switches with appropriate devices in H2PACK-7L or H2PACK-2L package and the C29 capacitance if needed.

The board components are easy to access and modify to make driver performance evaluation easier under different application conditions and fine adjustment of final application components.

Product status link

[EVSTGAP2SICSNC](#)

2 Bill of material

Table 1. EVSTGAP2SICSNC bill of material

Reference	Description	Value / generic part number
CN1, CN2, CN3	Tab FASTON 250 Horizontal	TE 928814-1
C1, C2, C8, C9	SMT ceramic capacitor	100 nF / 50 V
C3, C7, C10, C14	SMT ceramic capacitor	1 μ F / 50 V
C4, C11	SMT ceramic capacitor	N.M.
C5, C6, C12, C13	SMT ceramic capacitor	220 pF / 25 V
C15, C17, C19, C20, C22, C24	SMT ceramic capacitor	1 μ F / 50 V
C16, C21	SMT ceramic capacitor	4.7 μ F / 50 V
C18, C23	SMT ceramic capacitor	N.M.
C25	THT electrolytic capacitor	N.M.
C26, C27	SMT ceramic capacitor	N.M.
C28	Film capacitor	N.M.
C29	Film capacitor	33 nF / 1.25 kV
C30	SMT ceramic capacitor	10 μ F / 25 V
C31	SMT ceramic capacitor	4.7 μ F / 10 V
D1, D3	Automotive low drop power Schottky rectifier	STPS2L40ZFY
D2	High voltage ultrafast rectifier	STTH112A
D4, D8	Surface mount precision Zener diode	BZT585B18T
D5, D7	Surface mount precision Zener diode	BZT585B20T
D6, D9	Surface mount precision Zener diode	BZT585B2V7T
D10	Zener Voltage Regulator 500mW	MMSZ3V3T1G
D11	5.1 V 500 mW, Zener Voltage Regulator	MMSZ5V1T1G
FB1, FB2, FB3, FB4	Ferrite Beads	BLM21AG471SN1
JP1, JP7	SMT resistor	0 Ω
JP2, JP3, JP8, JP9	SMT resistor	N.M.
JP4, JP5, JP11, JP13, JP15, JP17, JP19, JP20, JP21	SMT resistor	0 Ω
JP6, JP10, JP12, JP14, JP16, JP18	SMT resistor	N.M.
J3, J4	Connector terminal block T.H. 2 POS 5.08 mm	N.M.
Q1A, Q2A	Alternative footprint for HPACK or DPACK	N.M.
Q1, Q2	Silicon carbide Power MOSFET 650 V, 55 m Ω typ., 45 A	SCTH35N65G2V
Q3, Q4	Low voltage fast-switching NPN power transistors	2STF1360
R1, R6	SMT resistor	39 Ω
R2, R8	SMT resistor	3.3 Ω
R3, R4, R7, R9	SMT resistor	100 Ω
R5	SMT resistor	N.M.

Reference	Description	Value / generic part number
R10, R12	SMT resistor	1 k Ω
R11, R13	SMT resistor	0 Ω
R14, R16	SMT resistor	10 M Ω
R15	SMT resistor	240 Ω
R17, R18	SMT resistor	N.M.
R19	SMT resistor	680 Ω
TP1, TP2, TP3, TP4, TP5, TP6, TP7, TP8, TP11, TP13, TP14, TP15, TP16, TP17	Test point - PCB 1.5 mm diameter	T POINT R
TP9, TP10, TP12	THT ring test point	TPTH-ANELLO-1MM
T1, T2	Common mode choke, SMD 4.7x4.5 mm	N.M.
U1, U2	Galvanically isolated 4 A single gate driver for SiC MOSFETs	STGAP2SICSNC
U3, U4	5.2 kVDC Isolated 2W Gate Drive DC/DC Converters	MGJ2D051509SC

3 Layout and component placements

Figure 3. EVSTGAP2SICSNC – Layout (component placement top view)

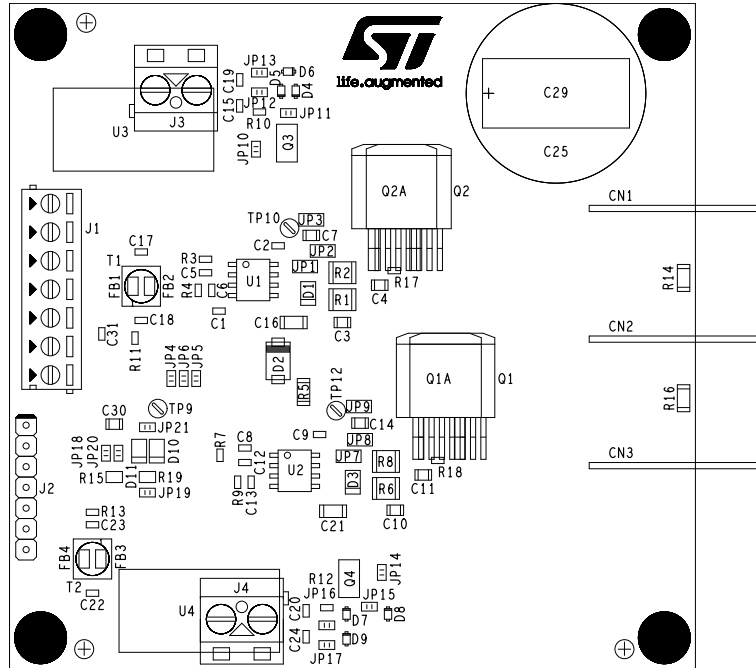


Figure 4. EVSTGAP2SiCSN – Layout (component placement bottom view)

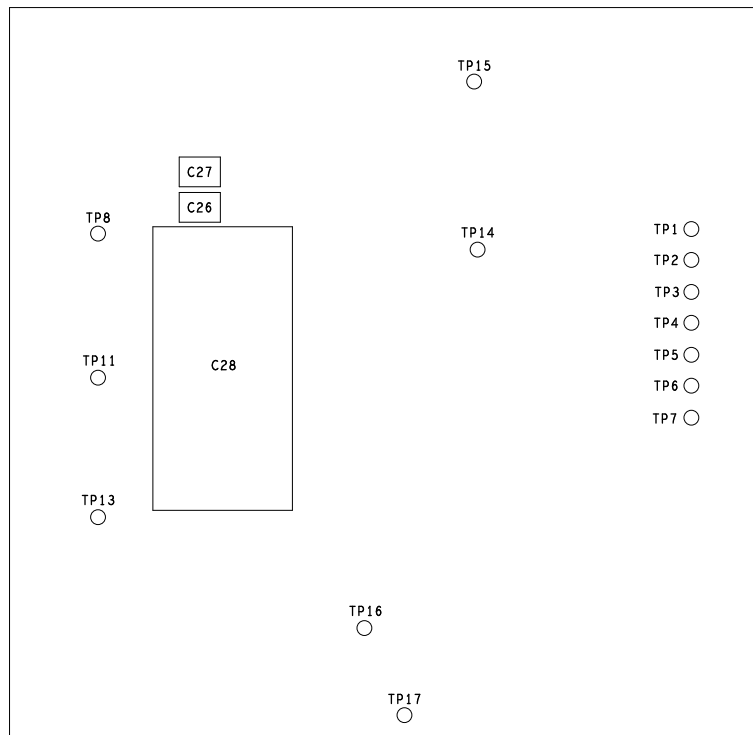


Figure 5. EVSTGAP2SICSN – Layout (top layer)

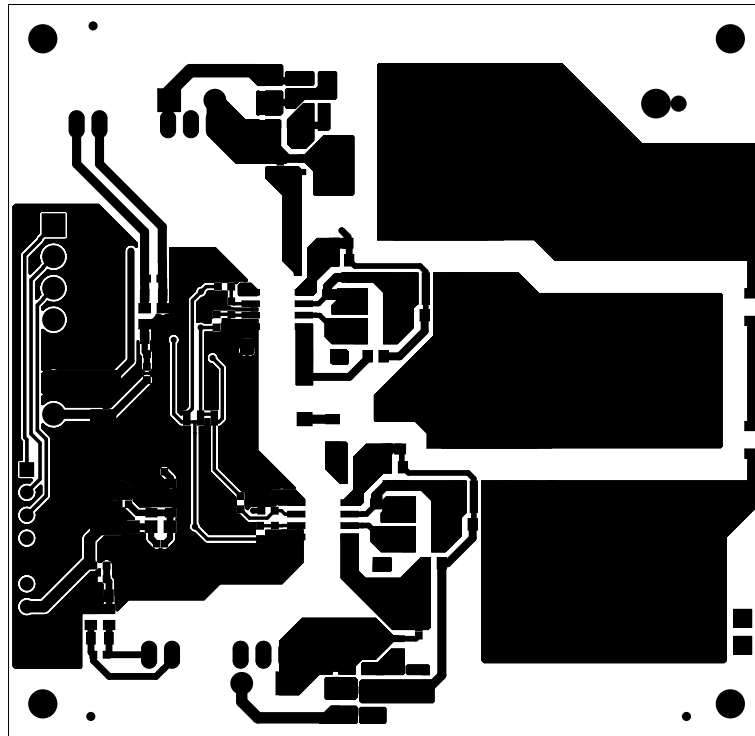
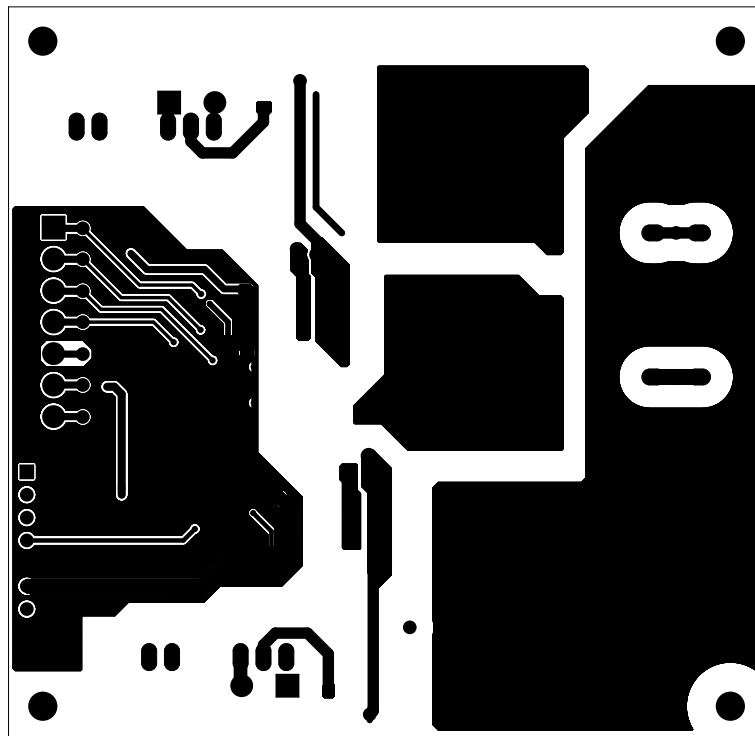


Figure 6. EVSTGAP2SICSN – Layout (bottom layer)



Revision history

Table 2. Document revision history

Date	Version	Changes
13-Aug-2021	1	Initial release.

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